

ABSTRACT

In a dry process after a cleaning process using a cleaning-liquid nozzle and a rinse process using a side rinse nozzle are performed on a wafer W, the wafer W is
5 turned, feeding of pure water to a center point of the wafer W from a pure-water nozzle is started, and substantially at the same, injection of a nitrogen gas from a gas nozzle to a center portion of the wafer W at a point at an adequate distance apart from the center of
10 the wafer W is started. Next, while the pure-water nozzle is caused to scan toward the periphery of the wafer W, the gas nozzle is caused to scan toward the periphery of the wafer W in an area radially inward of the position of the pure-water nozzle after the gas
15 nozzle passes the center of the wafer W.